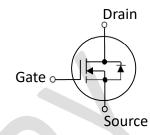




## 85V, 90A <sup>(1)</sup> N-Channel MOSFET

- Advanced Trench Device Design and Processes
- High Reliability Capability
- 100% CP Probing and Inking



SYMBOL

Electrical Characteristics in C/P Test (TJ at 25 °C)							
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Condition	
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	85	-	_	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250µA	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	-	_	6.5	mΩ	$V_{GS} = 10V, I_{D} = 1A(2)$	
V <sub>GS (th)</sub>	Gate Threshold Voltage	2.0	I	4.0	V	$V_{DS}$ = $V_{GS}$ , $I_D$ =250 $\mu$ A	
I <sub>DSS</sub>	Drain-to-Source Leakage Current			1	μA	V <sub>DS</sub> =85V, V <sub>GS</sub> =0V	
I <sub>GSS</sub>	Gate-Body Leakage Current	—	—	±100	nA	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature	-55°C to 150°C Max.					

Mechanical Data	Die Drawing	
Chip Size	3628 µm X 3086 µm	
Gate Pad Size	304 µm X 420 µm	
Source Pad Size	3114 μm X 2942 μm	
Scribe Line Width	60 µm	
Wafer Thickness	150 µm	
Wafer Diameter	200 mm	
Gross Die	2420 EA	
Source Metallization	Al-Cu (4 µm typical)	
Drain Metallization	Ti-Ni-Ag	
Passivation	N/A	
Recommended Storage Environment	Store in original container, in dry nitrogen, 6 months at ambient temperature of 23°C ± 3°C	1

(1) This characteristic assumes the die is assembled in TO-220 package. Actual performance may degrade when assembled.

(2) Pulse Width tp = < 300  $\mu$ S, Duty Cycle < 2%.

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